

Octal Bus Buffer Inverting MC74VHC540

The MC74VHC540 is an advanced high speed CMOS inverting octal bus buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHC540 features inputs and outputs on opposite sides of the package and two AND-ed active-low output enables. When either $\overline{\text{OE1}}$ or $\overline{\text{OE2}}$ are high, the terminal outputs are in the high impedance state.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 5.5 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

- High Speed: $t_{PD} = 3.7 \text{ ns}$ (Typ) at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4.0 \mu A$ (Max) at $T_A = 25$ °C
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise: V_{OLP} = 1.2 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 100 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 124 FETs or 31 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant

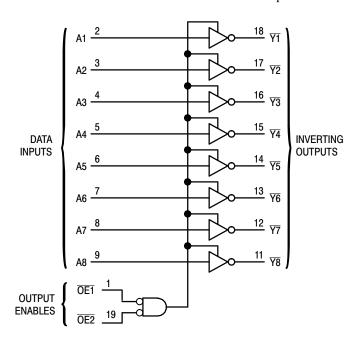


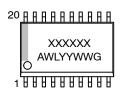
Figure 1. Logic Diagram

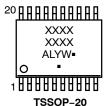




SOIC-20 DW SUFFIX CASE 751D TSSOP-20 DT SUFFIX CASE 948E

MARKING DIAGRAMS





SOIC-20 T

A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or • = Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT

OE1 [1●	20	□ v _{cc}
A1 [2	19	OE2
A2 [3	18] <u>Y1</u>
A3 [4	17] <u>Y2</u>
A4 [5	16] <u>73</u>
A5 [6	15	□ Y 4
A6 [7	14] <u>Y5</u>
A7 [8	13	□ <u>∀6</u>
A8 [9	12	□ Y7
GND [10	11	□ <u>Y8</u>

FUNCTION TABLE

	Inputs	Output \overline{Y}	
OE1	OE2	Α	Output Y
L	L	L	Н
L	L	Н	L
Н	Х	Х	Z
X	Н	Х	Z

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V _{CC}	DC Supply Voltage		-0.5 to +6.5	٧
V _{IN}	DC Input Voltage		-0.5 to +6.5	٧
V _{OUT}	DC Output Voltage		-0.5 to V _{CC} +0.5	V
I _{IN}	DC Input Current, per Pin		±20	mA
lout	DC Output Current, Per Pin		±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins		±75	mA
I _{IK}	Input Clamp Current		-20	mA
lok	Output Clamp Current		±20	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 secs		260	°C
TJ	Junction Temperature Under Bias		+150	°C
θJA	Thermal Resistance (Note 1)	SOIC-20W TSSOP-20	96 150	°C/W
P _D	Power Dissipation in Still Air at 25°C	SOIC-20W TSSOP-20	1302 833	mW
MSL	Moisture Sensitivity		Level 1	_
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.540 in	-
V _{ESD}	ESD Withstand Voltage (Note 2)	Human Body Model Charged Device Model	2000 N/A	V
I _{LATCHUP}	Latchup Performance (Note 3)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Measured with minimum pad spacing on an FR4 board, using 76 mm-by-114 mm, 2-ounce copper trace no air flow per JESD51-7.
 HBM tested to EIA / JESD22-A114-A. CDM tested to JESD22-C101-A. JEDEC recommends that ESD qualification to EIA/JESD22-A115A (Machine Model) be discontinued.
 3. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	5.5	V
V _{IN}	DC Input Voltage (Note 4)	0	5.5	V
V _{OUT}	DC Output Voltage (Note 4)	0	V _{CC}	V
T _A	Operating Temperature	-55	+125	°C
t _r , t _f	Input Rise or Fall Rate $ V_{CC} = 3.0 \text{V}_{CC} = 4.5 \text{V}_{$		100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

4. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC ELECTRICAL CHARACTERISTICS (MC74VHC540)

			v _{cc}	,	T _A = 25°C		T _A = - 55	to 125°C	
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V _{CC} x 0.7			1.50 V _{CC} x 0.7		V
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 V _{CC} x 0.3		0.50 V _{CC} x 0.3	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu\text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
		$V_{in} = V_{IH} \text{ or } V_{IL} \\ I_{OH} = -4 \text{ mA} \\ I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		-
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44	
l _{in}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	0 to 5.5			±0.1		±1.0	μА
I _{OZ}	Maximum Three-State Leakage Current	V _{in} = V _{IL} or V _{IH} V _{out} = V _{CC} or GND	5.5			±0.25		±2.5	μΑ
I _{CC}	Maximum Quiescent Supply Current	V _{in} = V _{CC} or GND	5.5			4.0		40.0	μА

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (MC74VHC540)

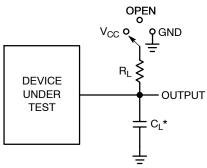
					T _A = 25°C		T _A = - 55	to 125°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to ₹ (Figures 1 and 3)	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C _L = 15 pF C _L = 50 pF		4.8 7.3	7.0 10.5	1.0 1.0	8.5 12.0	ns
	(Figures Failu 3)	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 15 pF C _L = 50 pF		3.7 5.2	5.0 7.0	1.0 1.0	6.0 8.0	
t _{PZL} , t _{PZH}	Output Enable Time, OEn to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C _L = 15 pF C _L = 50 pF		6.8 9.3	10.5 14.0	1.0 1.0	12.5 16.0	ns
	(Figures 2 and 4)	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 15 pF C _L = 50 pF		4.7 6.2	7.2 9.2	1.0 1.0	8.5 10.5	
t _{PLZ} ,	Output Disable Time,	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C _L = 50 pF		11.2	15.4	1.0	17.5	ns
t _{PHZ}	(Figures 2 and 4)	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 50 pF		6.0	8.8	1.0	10.0	
t _{OSLH} , t _{OSHL}	Output to Output Skew	V _{CC} = 3.3 ± 0.3V (Note 5)	C _L = 50 pF			1.5			ns
		V _{CC} = 5.0 ± 0.5V (Note 5)	C _L = 50 pF			1.0			ns
C _{in}	Maximum Input Capacitance				4	10		10	pF
C _{out}	Maximum Three–State Output Capacitance (Output in High Impedance State)				6				pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Note 6)	17	pF

NOISE CHARACTERISTICS (MC74VHC540)

		T _A = 25°C		
Symbol	Parameter	Тур Мах		Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.9	1.2	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.9	-1.2	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

 ^{5.} Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
 6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per bit). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.



 $^{^{\}star}C_L$ Includes probe and jig capacitance Input signal $t_R=t_F=3\ ns$

Test	Switch Position	CL	RL
t _{PLH} / t _{PHL}	Open	See AC Characteristics	1 kΩ
t _{PLZ} / t _{PZL}	V _{CC}	Table	
t _{PHZ} / t _{PZH}	GND		

Figure 2. Test Circuits

SWITCHING WAVEFORMS

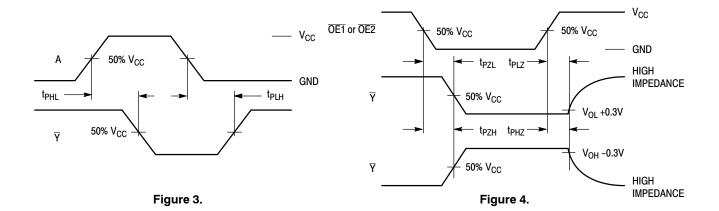


Figure 5. Input Equivalent Circuit

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
MC74VHC540DWR2G	VHC540G	SOIC-20 WB	1000 / Tape & Reel
MC74VHC540DTR2G	VHC 540	TSSOP-20	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

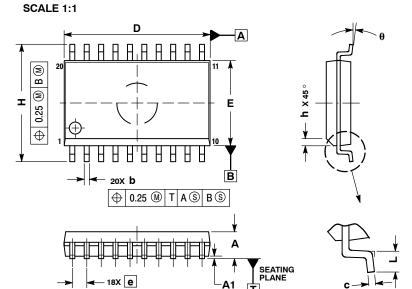
*-Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable





SOIC-20 WB CASE 751D-05 **ISSUE H**

DATE 22 APR 2015



- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

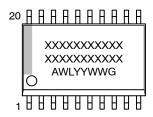
	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
b	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
E	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
θ	0°	7 °		

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

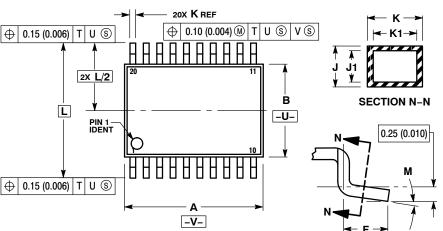
0.100 (0.004)

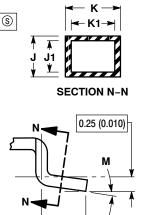
-T- SEATING

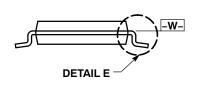


TSSOP-20 WB CASE 948E ISSUE D

DATE 17 FEB 2016







DETAIL E

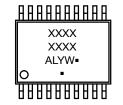
NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION.
 SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
Ĺ	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

GENERIC MARKING DIAGRAM*



= Assembly Location

= Wafer Lot

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

◀	7.06
1	
	PITCH
16X 0.36 126	─
0.36 -	DIMENSIONS: MILLIMETERS

SOLDERING FOOTPRINT

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